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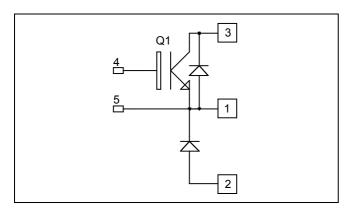






## Buck Chopper Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 1200V$$
  
 $I_{C} = 300A$  @  $T_{C} = 80^{\circ}C$ 



### **Application**

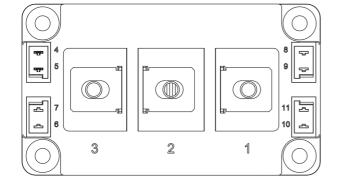
- AC and DC motor control
- Switched Mode Power Supplies

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

#### **Benefits**

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant



### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_{\rm C}$	Continuous Collector Current	$T_C = 25^{\circ}C$	440	
	Continuous Conector Current	$T_C = 80$ °C	300	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25$ °C	1450	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	600A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				500	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.7	2.1	V
$V_{CE(sat)}$	Conector Emitter saturation voltage	$I_C = 300A$ $T_j = 125^\circ$	$T_j = 125$ °C		2.0		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 12mA$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V ; V_{CE} = 25V$ f = 1MHz			21		nF
$C_{res}$	Reverse Transfer Capacitance				1		Ш
$Q_{G}$	Gate charge	$V_{GE}$ =±15V, $I_{C}$ =300A $V_{CE}$ =600V			2.8		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (25°C)		250		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			90		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 300A$			550		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 2.2\Omega$		130			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (125°C)		300		ng
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			100		
$T_{d(off)}$	Turn-off Delay Time		$V_{Bus} = 600V$ $I_{C} = 300A$ $R_{G} = 2.2\Omega$		650		ns
$T_{\rm f}$	Fall Time	C			180		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 300A$ $R_{G} = 2.2\Omega$	$T_j = 125$ °C		25		mJ
$E_{\text{off}}$	Turn off Energy		$T_j = 125$ °C		44		1113
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10 \mu s$ ; $T_i = 125 ^{\circ}C$			1200		A

Reverse diode ratings and characteristics

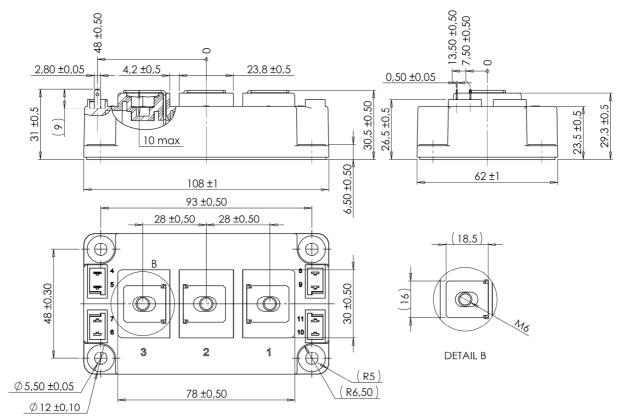
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V	
$I_{RRM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			750 1000	μА	
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		300		A	
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 300A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2.1	V	
V F	Diode Forward Voltage		$T_j = 125$ °C		1.6		v	
+	Reverse Recovery Time		$T_j = 25^{\circ}C$		170		ns	
t <sub>rr</sub>			$T_j = 125$ °C		280			
0	Reverse Recovery Charge	$I_F = 300A$ $V_R = 600V$ $di/dt = 3500A/\mu s$	$I_{i} = 25^{\circ}$	$T_j = 25$ °C		28		μС
$Q_{rr}$	Reverse Recovery Charge		$T_j = 125$ °C		56		μС	
Е	Reverse Recovery Energy		$T_j = 25$ °C		12		mJ	
$E_{rr}$			$T_{\rm j} = 125^{\circ}{\rm C}$		22		1113	



## Thermal and package characteristics

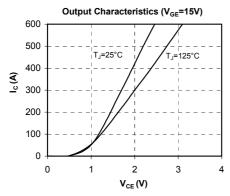
Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.085	°C/W
1\(\text{thJC}\)			Diode			0.16	C/ W
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		150	
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting forque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	18.111
Wt	Package Weight					350	g

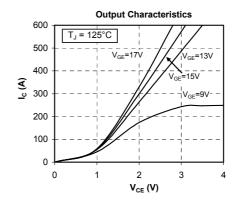
## D3 Package outline (dimensions in mm)

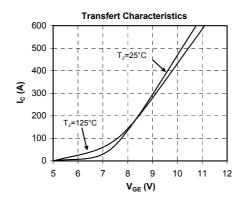


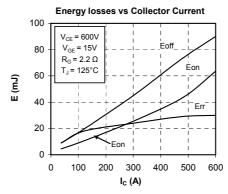


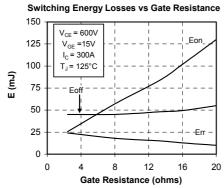
### **Typical Performance Curve**

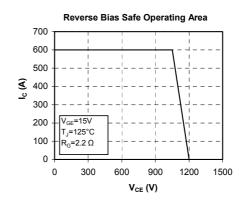


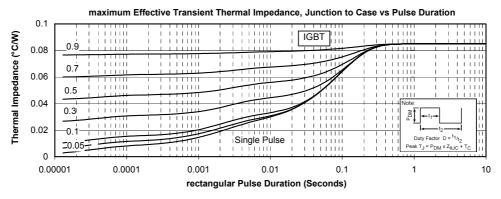




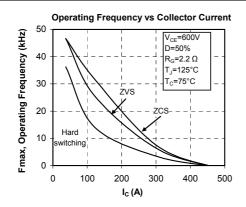


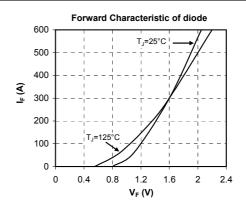


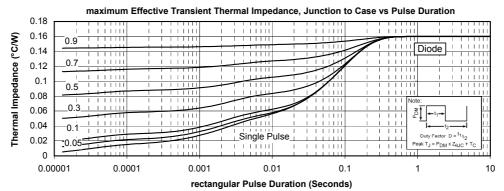












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